

ABSTRACT OF THE DISCLOSURE

The invention encompasses a method of forming a silicon-doped aluminum oxide. Aluminum oxide and silicon monoxide are co-evaporated. Subsequently, at least some of the evaporated aluminum oxide and silicon monoxide is deposited on a substrate to form the silicon-doped aluminum oxide on the substrate. The invention also encompasses methods of forming transistors and flash memory devices.

1
2
3
4
5
6
7
8
9
10
11
12
13
14
15
16
17
18
19
20
21
22
23

00754935-040404